100V N-Ch Power MOSFET

V_{DS}		100	V
$R_{DS(on),typ}$	V_{GS}=10V	8.4	m
$R_{DS(on),typ}$	V_{GS}=4.5V	11.3	m
$I_{D\ (Sillicon\ Limited)}$		65.9	A
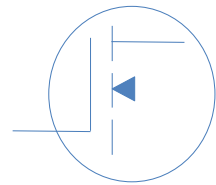
Part Number	Package	Marking
HGD098N10AL	TO-252	GD098N10AL
HGI098N10AL	TO-251	GI098N10AL

Absolute Maximum Ratings at T_J=25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C=25℃	66	A
		T_C=100℃	47	
Drain to Source Voltage	V_{DS}	-	100	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	160	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.1mH, T_C=25℃	31	mJ
Power Dissipation	P_D	T_C=25℃	94	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	℃

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Ambient	R_{JA}	50	℃/W
Thermal Resistance Junction-Case	R_{JC}	1.6	℃/W

Electrical Characteristics at T_J=25℃ (unless otherwise specified)
Static Characteristics

Parameter	Symbol		min		max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250 A		-	-	
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250 A	1.4	1.8	2.4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=100V, T_j=25℃	-	-	1	A
		V_{GS}=0V, V_{DS}=100V, T			100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A	-	8.4	9.8	m
		V_{GS}=4.5V, I_D=20A	-	11.3	13	
Transconductance	g_{fs}	V_{DS}=5V, I_D=10A	-	80	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz	-	1.4	-	

Dynamic Characteristics

Parameter	Symbol		min		max	
Input Capacitance	C_{iss}		-	1450	-	
Output Capacitance	C_{oss}	V_{GS}=0V, V_{DS}=50V, f=1MHz	-	273	-	pF
Reverse Transfer Capacitance	C_{rss}		-	5.0	-	
Total Gate Charge	Q_g(10V)		-	24	-	
Total Gate Charge	Q_g(4.5V)	V_{DD}=50V, I_D=20A, V_{GS}=10V	-	12	-	nC
Gate to Source Charge	Q_{gs}		-	4	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	6	-	
Turn on Delay Time	$t_{d(on)}$		-	6	-	
Rise time	t_r	V_{DD}=50V, I_D=20A, V_{GS}=10V,	-	4	-	ns
Turn off Delay Time	$t_{d(off)}$	R_G=10 ,	-	18	-	
Fall Time	t_f		-	3	-	

Reverse Diode Characteristics

Parameter	Symbol		min		max	
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=50V, I_F=20A, dI_F/dt=500A/ s	-	40	-	ns
Reverse Recovery Charge	Q_{rr}		-	152	-	nC

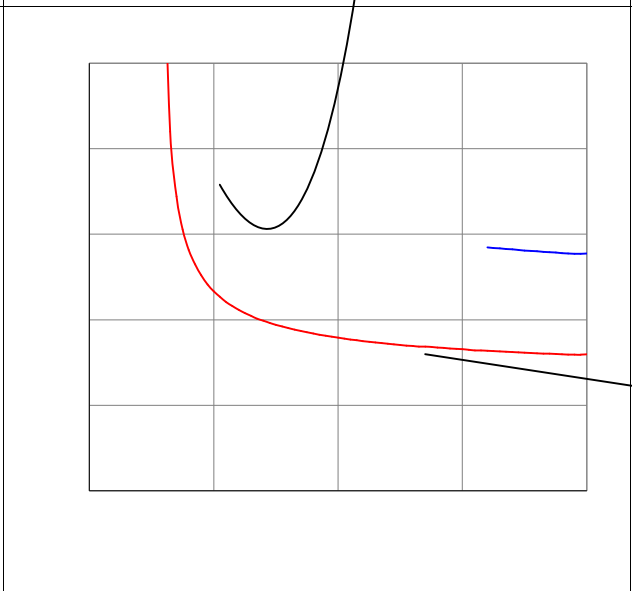| Fig 1. Typical Output Characteristics	Figure 2. On-Resistance vs. Gate-Source Voltage
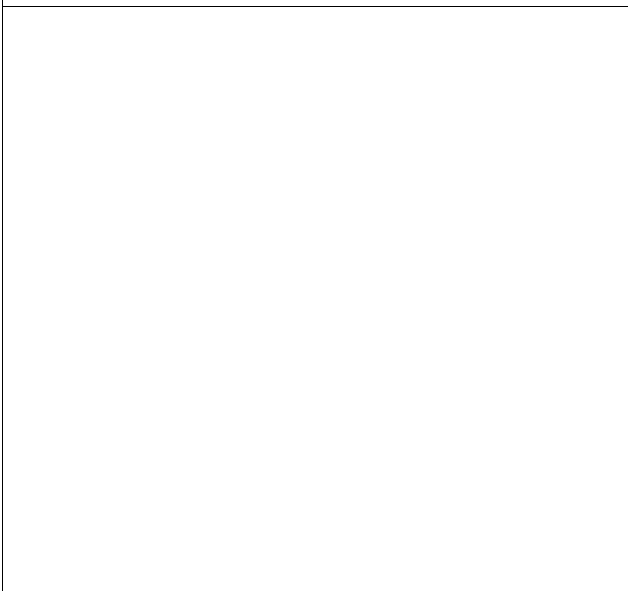
Figure 3. On-Resistance vs. Drain Current and Gate Voltage

V_{GS}=4.5V

V_{GS}=10V

$R_{DS(ON)}$ (m)

I_D (A)

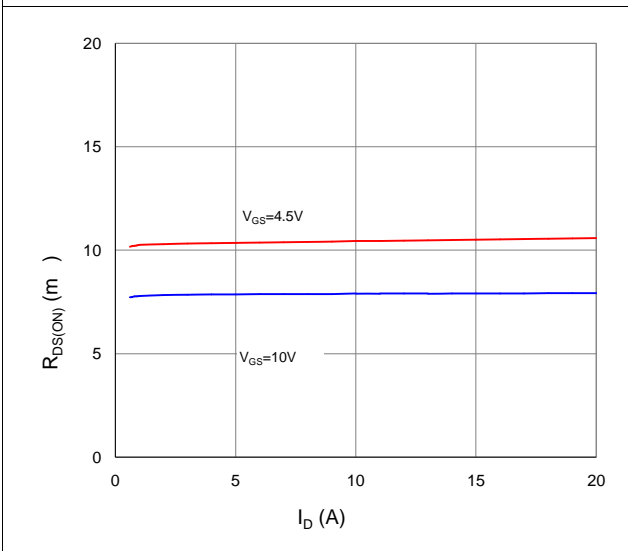Figure 4. Normalized On-Resistance vs. Junction Temperature

I_D=20A

V_{GS}=10V

V_{GS}=4.5V

Normalized On-Resistance

Temperature (°C)
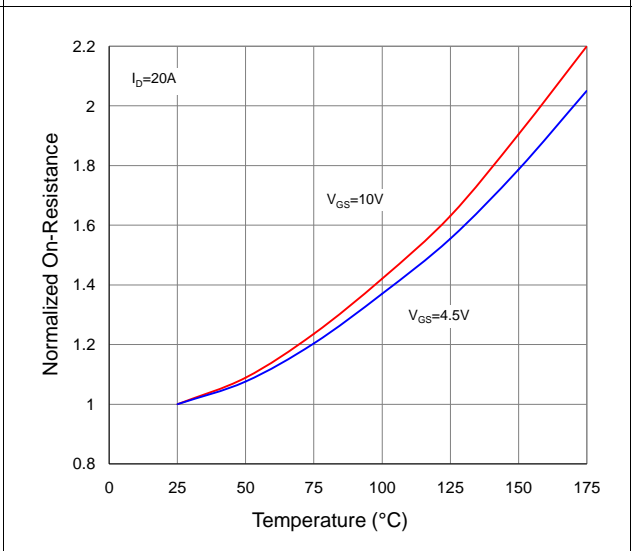
Figure 5. Typical Transfer Characteristics
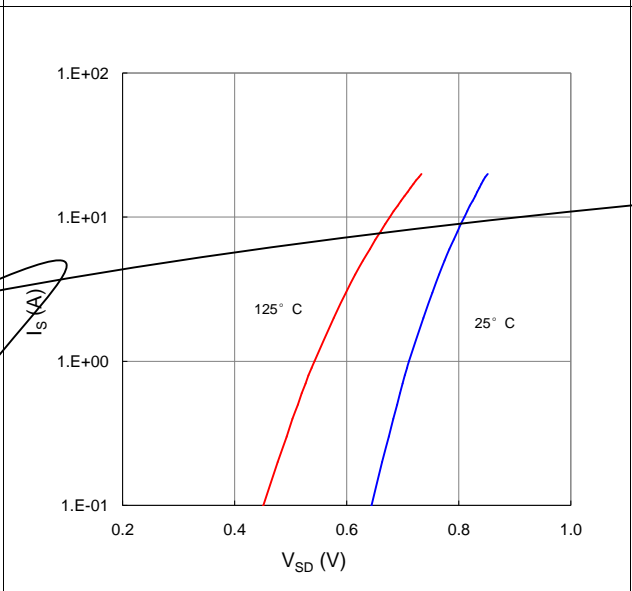
Figure 6. Typical Source-Drain Diode Forward Voltage

1.E+02

1.E+01

1.E+00

1.E-01

I_S (A)

125° C

25° C

V_{SD} (V)

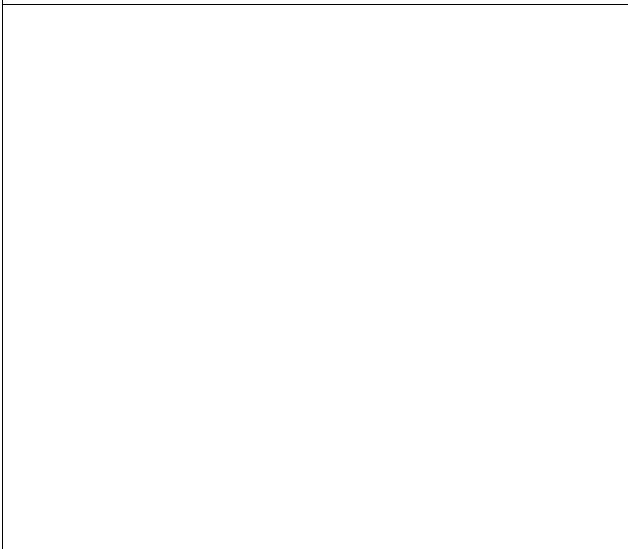| Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage	Figure 8. Typical Capacitance vs. Drain-to-Source Voltage
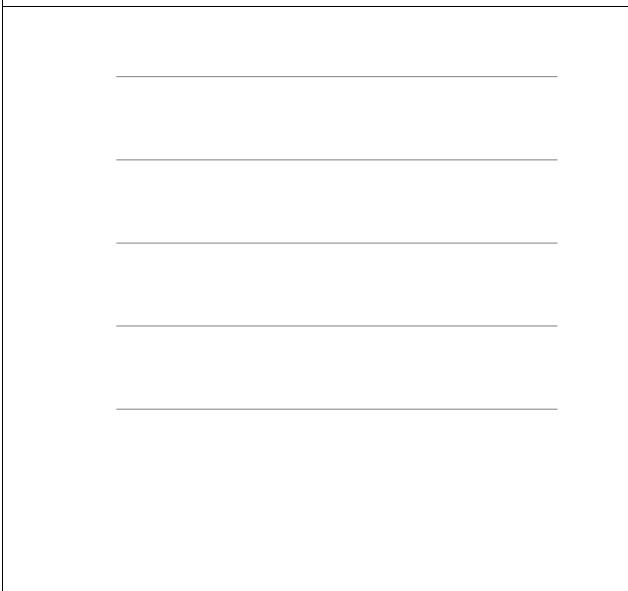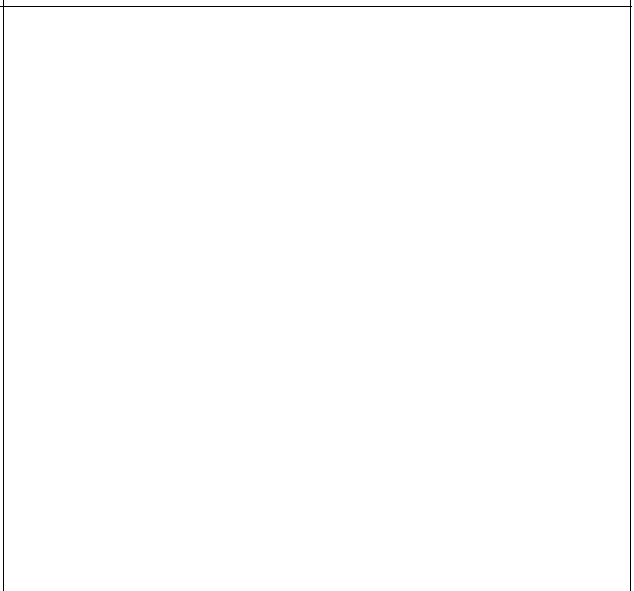
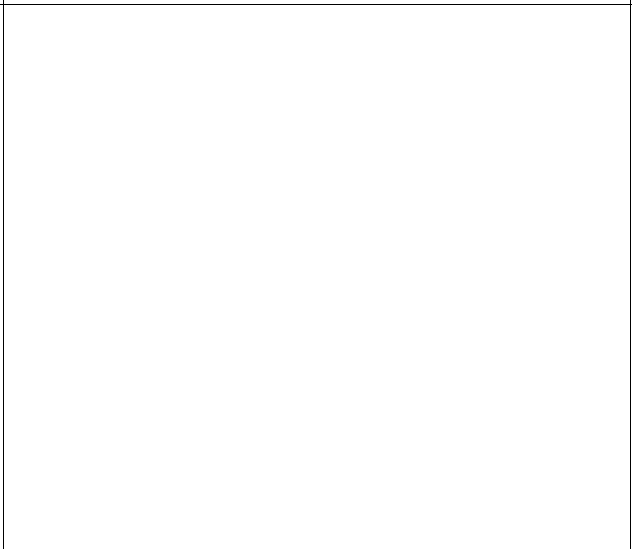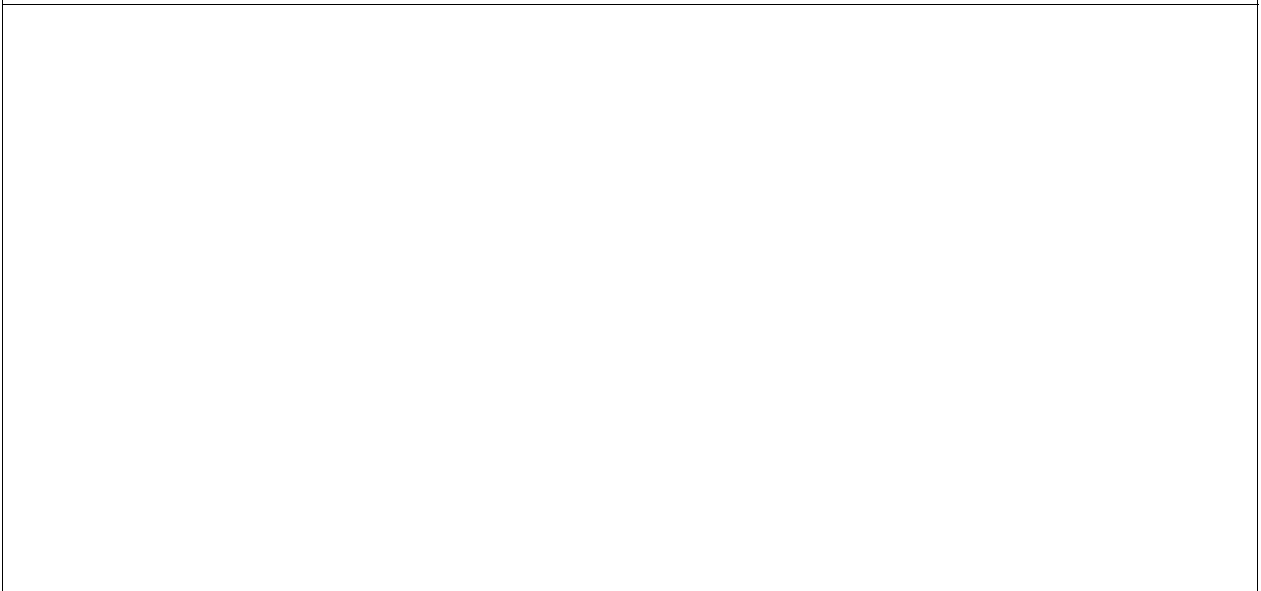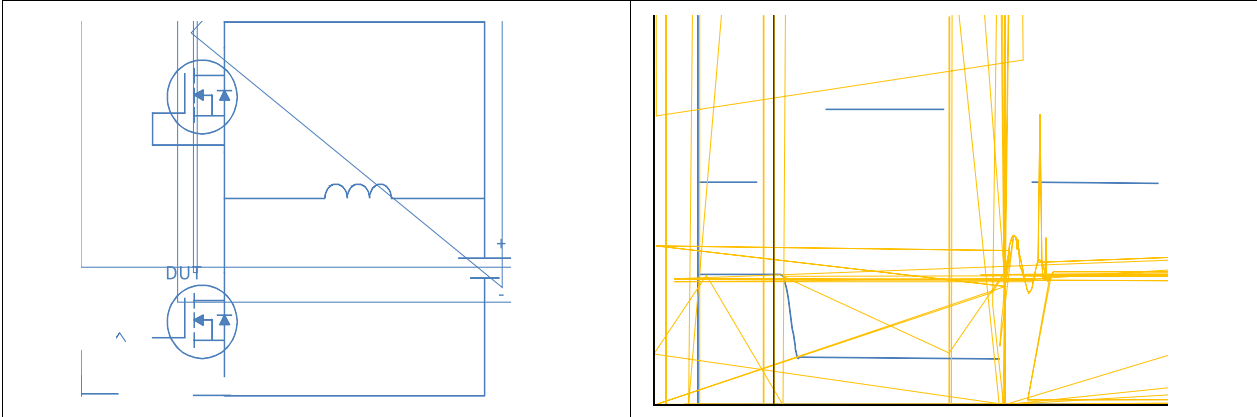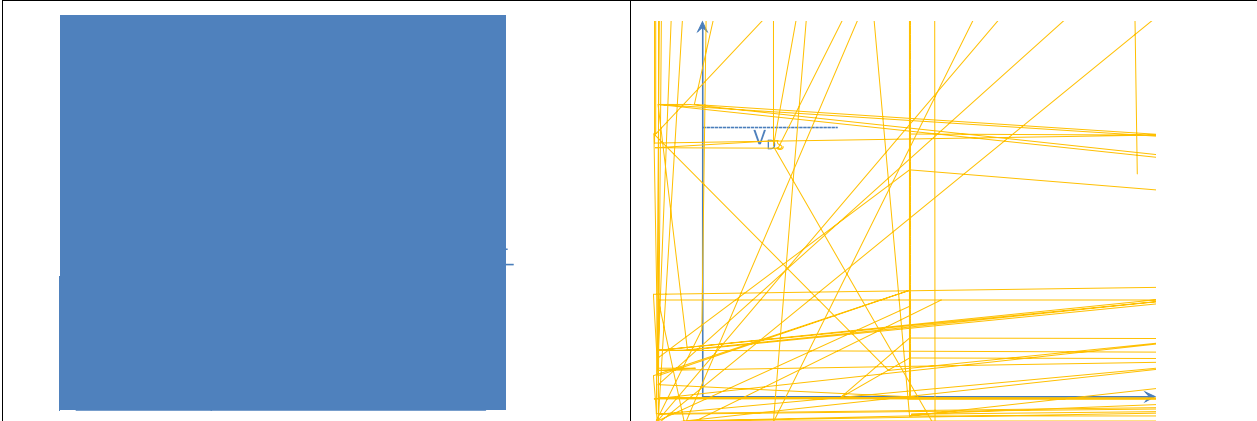| Figure 9. Maximum Safe Operating Area	Figure 10. Maximun Drain Current vs. Case Temperature

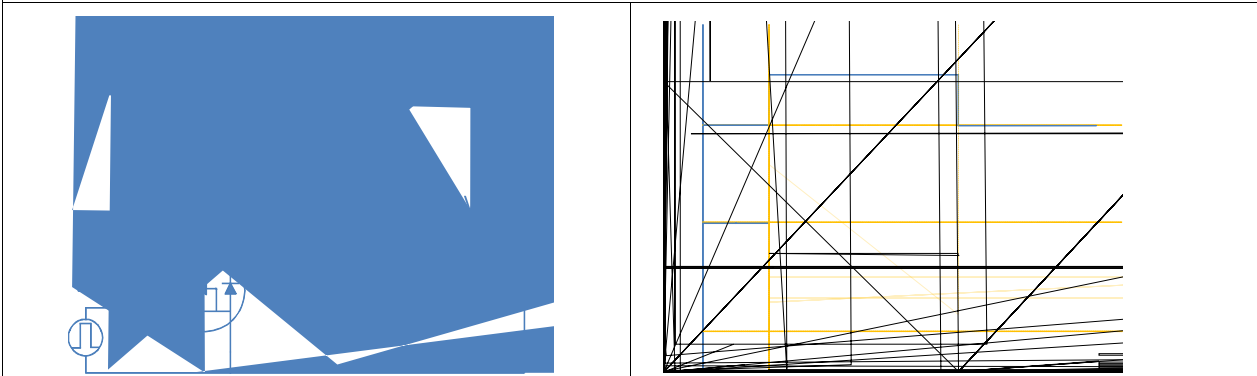Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient
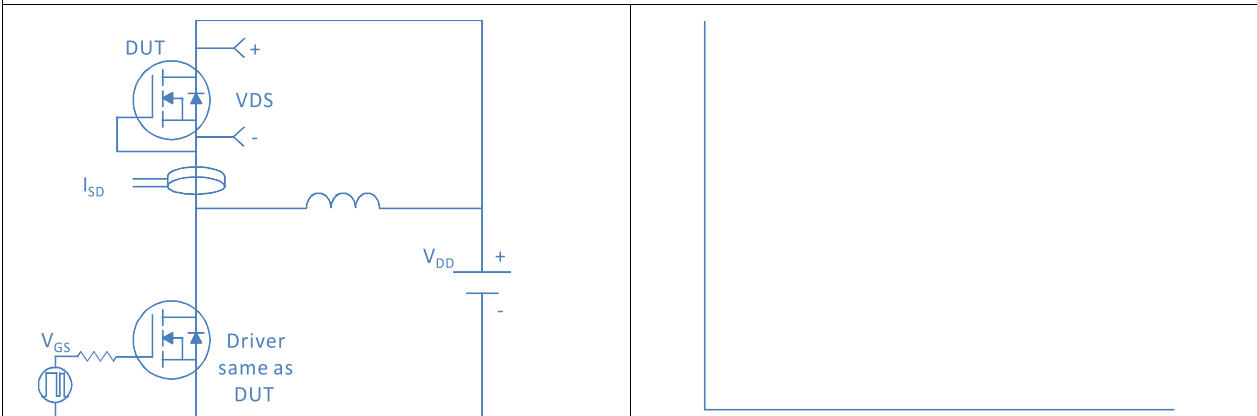
Inductive switching Test

Gate Charge Test

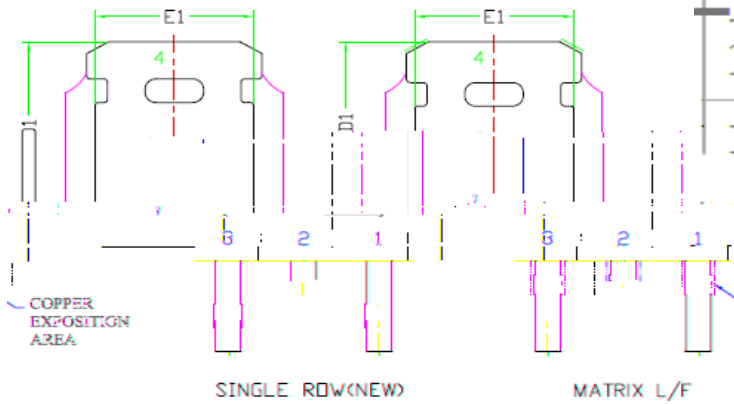## Uclamped Inductive Switching (UIS) Test

Diode Recovery Test

Package Outline

TO-252, 2 leads

SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1	2.743 REF		
L2	0.508 BSC		
L3	0.89	--	1.27
L4	0.64	--	1.01
L5	--	--	--
D	6.00	6.10	6.223

COPPER
EXPOSITION
AREA

SINGLE ROW(NEW)   MATRIX L/F

Package Outline

TO-251, 3leads
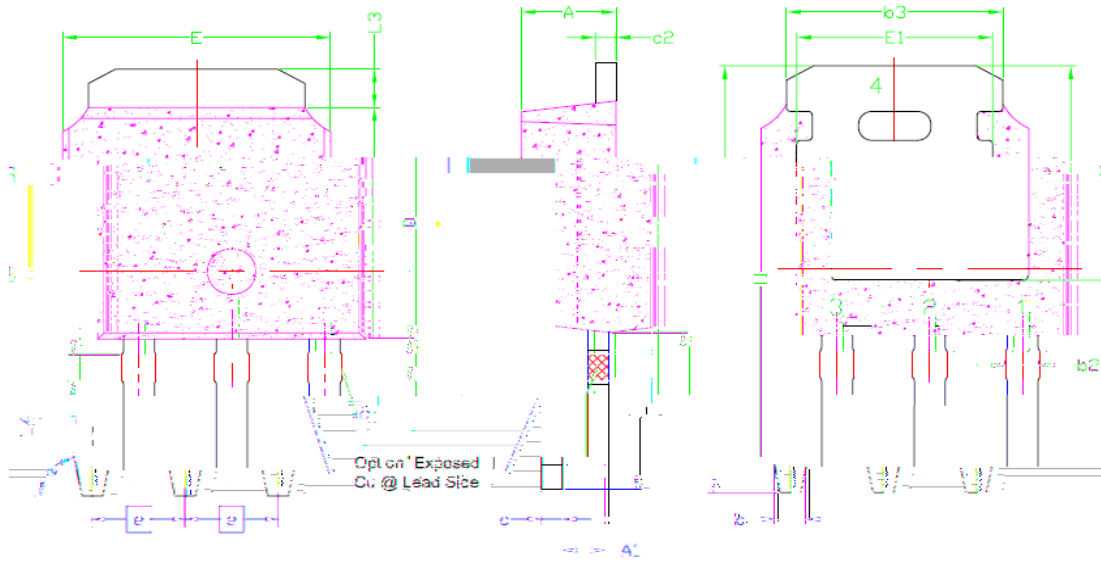
SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	3.98	4.13	4.28
L3	0.89	--	1.27
L4	0.698 REF		
L5	0.972	1.099	1.226
D	6.00	6.10	6.223
H	11.05	11.25	11.45
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
e	2.286 BSC		
A	2.20	2.30	2.38
A1	0.89	1.04	1.15
c	0.46	0.50	0.60
c2	0.46	0.50	0.60
D1	5.10	--	--
E1	4.40	--	--
α	79° REF		